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Reg. No. :

Question Paper Code : 40431

B.E./B.Tech. DEGREE EXAMINATIONS, NOVEMBER/DECEMBER 2021.

Sixth/Seventh Semester

Electronics and Communication Engineering

EC 8095 - VLSI DESIGN

(Common to : B.E. Electrical and Electronics Engineering/B.E. Electronics and Instrumentation Engineering/B.E. Electronics and Telecommunication Engineering/ B.E. Instrumentation and Control Engineering/B.E. Robotics and Automation)

(Regulations 2017)

Time : Three hours

Maximum : 100 marks

Answer ALL questions. PART A $-(10 \times 2 = 20 \text{ marks})$

- 1. How does a transmission gate produce fully restored logic output?
- 2. Define low noise margin and high noise margin of a CMOS inverter.
- 3. State the operations performed during pre charge and evaluate phase of dynamic circuits.
- 4. List the sources of power dissipation in CMOS circuits.
- 5. What is meant by bistability?
- 6. Define clock skew in digital circuits.
- 7. Draw the circuit diagram of 1-bit binary shifter using MOS transistor.
- 8. State the need of a sense amplifier in a memory cell.
- 9. List the common techniques for ad hoc testing.
- 10. What are the limitations of IDDQ testing?

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PART B — $(5 \times 13 = 65 \text{ marks})$

 (a) Derive the expression for current in cutoff, linear and saturation region in long channel I-V characteristics.

Or

- (b) Draw and explain the equivalent RC circuit for an Inverter.
- 12. (a) Compare the circuit implementation of 2-input multiplexer using static CMOS, domino and dual-rail domino logic.

Or

- (b) Describe how dynamic voltage scaling can reduce dynamic power dissipation.
- 13. (a) Explain the circuit and working of CMOS implementation of schmitt trigger.

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- (b) Discuss the timing parameters that characterize the timing of sequential circuit.
- 14. (a) Elaborate on rotate right and rotate left operations using barrel shifters.

Or

- (b) Draw the NOR and NAND implementation of 4-word, 4-bit ROM.
- 15. (a) Describe the built-in self-test procedure.

Or

(b) Explain the factors to be considered to optimize circuits for manufacturability.

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PART C — $(1 \times 15 = 15 \text{ marks})$

16. (a) Design a 4-bit incrementer / decrementer using the CMOS design for 1-bit incrementer / decrementer. The 1-bit logic cell designed has a control input to control the increment or decrement operation. The truth table for 1-bit incrementer cell is as shown in Table 1.

Inputs			Output	
Clock	Ci	Qn-1	Ci+1	Qn
0	0	0	0	0
1	0	0	0	0
0	1	0	0	0
1	1	0	0	1
1	1	0	0	1
0	0	1	0	0
1	0	1	0	1
0	1	1	0	0
1	1	1	1	0

Table 1. Truth table for 1-bit incrementer cell

\mathbf{Or}

(b) Design a circuit described by the Boolean Function $Y = \overline{A.(B+C)(D+E)}$ using CMOS logic. Calculate the equivalent CMOS inverter circuit for simultaneous switching of all inputs assuming that $\left[\frac{w}{L}\right] = 5$ for pMOS

transistor and $\left[\frac{w}{L}\right] = 2$ for all nMOS transistor.

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